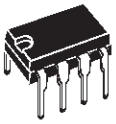
查询L6561供应商

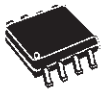
L6561

POWER FACTOR CORRECTOR

- VERY PRECISE ADJUSTABLE OUTPUT OVERVOLTAGE PROTECTION
- MICRO POWER START-UP CURRENT (50µA TYP.)
- VERY LOW OPERATING SUPPLY CURRENT (4mA TYP.)
- INTERNAL START-UP TIMER
- CURRENT SENSE FILTER ON CHIP
- DISABLE FUNCTION
- 1% PRECISION (@ T_j = 25°C) INTERNAL REFERENCE VOLTAGE
- TRANSITION MODE OPERATION
- TOTEM POLE OUTPUT CURRENT: ±400mA
- DIP8/SO8 PACKAGES



Minidip



SO8

ORDERING NUMBERS:
L6561 (Minidip)
L6561D (SO8)

DESCRIPTION

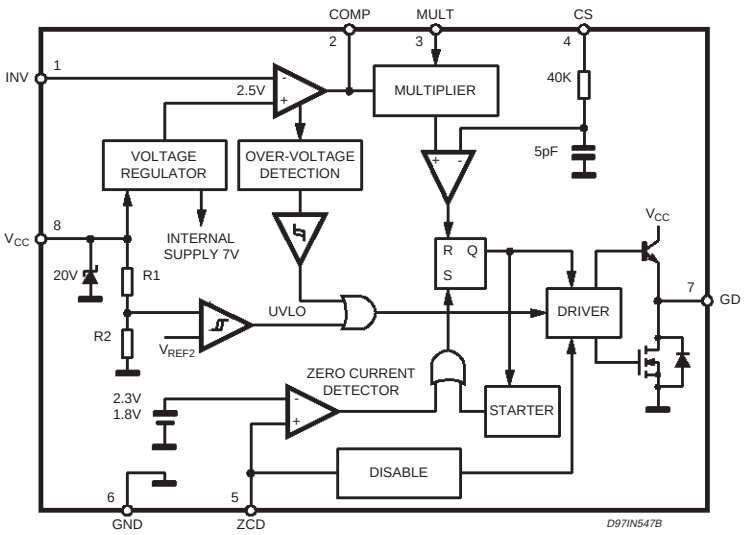
L6561 is the improved version of the L6560 standard Power Factor Corrector. Fully compatible with the standard version, it has a superior performant multiplier making the device capable of working in wide input voltage range applications (from 85V to 265V) with an excellent THD. Furthermore the start up current has been reduced at few tens of µA and a disable function has been implemented on the ZCD pin, guaranteeing lower current consumption in stand by mode.

Realised in mixed BCD technology, the chip gives the following benefits:

- **micro power start up current**
- **1% precision internal reference voltage (Tj = 25°C)**
- **Soft Output Over Voltage Protection**
- **no need for external low pass filter on the current sense**
- **very low operating quiescent current minimises power dissipation**

The totem pole output stage is capable of driving a Power MOS or IGBT with source and sink currents of +/- 400mA. The device is operating in transition mode and it is optimised for Electronic Lamp Ballast application, AC-DC adaptors and SMPS.

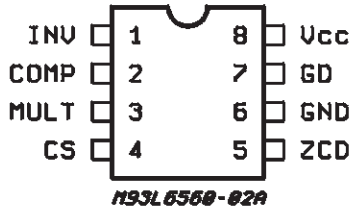
BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Pin	Parameter	Value	Unit
I_{Vcc}	8	$I_{CC} + I_Z$	30	mA
I_{GD}	7	Output Totem Pole Peak Current (2µs)	±700	mA
INV, COMP MULT	1, 2, 3	Analog Inputs & Outputs	-0.3 to 7	V
CS	4	Current Sense Input	-0.3 to 7	V
ZCD	5	Zero Current Detector	50 (source) -10 (sink)	mA mA
P_{tot}		Power Dissipation @T_{amb} = 50 °C **(Minidip)** **(SO8)**	1 0.65	W
T_j		Junction Temperature Operating Range	-25 to 150	°C
T_{stg}		Storage Temperature	-55 to 150	°C

PIN CONNECTION



THERMAL DATA

Symbol	Parameter	SO 8	MINIDIP	Unit
$R_{th\ j\text{-}amb}$	Thermal Resistance Junction-ambient	150	100	°C/W

PIN FUNCTIONS

N.	Name	Function
1	INV	Inverting input of the error amplifier. A resistive divider is connected between the output regulated voltage and this point, to provide voltage feedback.
2	COMP	Output of error amplifier. A feedback compensation network is placed between this pin and the INV pin.
3	MULT	Input of the multiplier stage. A resistive divider connects to this pin the rectified mains. A voltage signal, proportional to the rectified mains, appears on this pin.
4	CS	Input to the comparator of the control loop. The current is sensed by a resistor and the resulting voltage is applied to this pin.
5	ZCD	Zero current detection input. If it is connected to GND, the device is disabled.
6	GND	Current return for driver and control circuits.
7	GD	Gate driver output. A push pull output stage is able to drive the Power MOS with peak current of 400mA (source and sink).
8	V_{CC}	Supply voltage of driver and control circuits.

ELECTRICAL CHARACTERISTICS (V_{CC} = 14.5V; T_{amb} = -25°C to 125°C; unless otherwise specified)

SUPPLY VOLTAGE SECTION

Symbol	Pin	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_{CC}	8	Operating Range	after turn-on	11		18	V
$V_{CC\ ON}$	8	Turn-on Threshold		11	12	13	V
$V_{CC\ OFF}$	8	Turn-off Threshold		8.7	9.5	10.3	V
Hys	8	Hysteresis		2.2	2.5	2.8	V

SUPPLY CURRENT SECTION

Symbol	Pin	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$I_{START-U}$	8	Start-up Current	before turn-on (V_{CC} =11V)	20	50	90	µA
I_q	8	Quiescent Current			2.6	4	mA
I_{CC}		Operating Supply Current	C_L = 1nF @ 70KHz		4	5.5	mA
			in OVP condition V_{pin1} = 2.7V		1.4	2.1	mA
I_q		Quiescent Current	$V_{PIN5} \leq$ 150mV, $V_{CC} > V_{CC\ off}$		1.4	2.1	mA
			$V_{PIN5} \leq$ 150mV, $V_{CC} < V_{CC\ off}$	20	50	90	µA
V_Z	8	Zener Voltage	I_{CC} = 25mA	18	20	22	V

ERROR AMPLIFIER SECTION

Symbol	Pin	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_{INV}	1	Voltage Feedback Input Threshold	T_{amb} = 25°C	2.465	2.5	2.535	V
			12V < V_{CC} < 18V	2.44		2.56	
		Line Regulation	V_{CC} = 12 to 18V		2	5	mV
I_{INV}	1	Input Bias Current			-0.1	-1	µA
G_V		Voltage Gain	Open loop	60	80		dB
GB		Gain Bandwidth			1		MHz
I_{COMP}	2	Source Current	V_{COMP} = 4V, V_{INV} = 2.4V	-2	-4	-8	mA
		Sink Current	V_{COMP} = 4V, V_{INV} = 2.6V	2.5	4.5		mA
V_{COMP}	2	Upper Clamp Voltage	I_{SOURCE} = 0.5mA		5.8		V
		Lower Clamp Voltage	I_{Sink} = 0.5mA		2.25		V

MULTIPLIER SECTION

Symbol	Pin	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_{MULT}	3	Linear Operating Voltage		0 to 3	0 to 3.5		V
$\frac{\Delta V_{CS}}{\Delta V_{mult}}$		Output Max. Slope	V_{MULT} = from 0V to 0.5V V_{COMP} = Upper Clamp Voltage	1.65	1.9		
K		Gain	V_{MULT} = 1V V_{COMP} = 4V	0.45	0.6	0.75	1/V

CURRENT SENSE COMPARATOR

Symbol	Pin	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_{CS}	4	Current Sense Reference Clamp	V_{MULT} = 2.5V V_{COMP} = Upper Clamp Voltage	1.6	1.7	1.8	V
I_{CS}	4	Input Bias Current	V_{OS} = 0		-0.05	-1	µA
$t_{d\ (H-L)}$	4	Delay to Output			200	450	ns
	4	Current Sense Offset			0	15	mV

ELECTRICAL CHARACTERISTICS (continued)

ZERO CURRENT DETECTOR

Symbol	Pin	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_{ZCD}	5	Input Threshold Voltage Rising Edge	(1)		2.1		V
		Hysteresis	(1)	0.3	0.5	0.7	V
V_{ZCD}	5	Upper Clamp Voltage	I_{ZCD} = 20µA	4.5	5.1	5.9	V
V_{ZCD}	5	Upper Clamp Voltage	I_{ZCD} = 3mA	4.7	5.2	6.1	V
V_{ZCD}	5	Lower Clamp Voltage	I_{ZCD} = –3mA	0.3	0.65	1	V
I_{ZCD}	5	Sink Bias Current	$1V \le V_{ZCD} \le 4.5V$		2		µA
I_{ZCD}	5	Source Current Capability		-3		-10	mA
I_{ZCD}	5	Sink Current Capability		3		10	mA
V_{DIS}	5	Disable threshold		150	200	250	mV
I_{ZCD}	5	Restart Current After Disable	V_{ZCD} < Vdis; V_{CC} > V_{CCOFF}	-100	-200	-300	µA

OUTPUT SECTION

V_{GD}	7	Dropout Voltage	$I_{GDsource}$ = 200mA		1.2	2	V
			$I_{GDsource}$ = 20mA		0.7	1	V
			I_{GDsink} = 200mA			1.5	V
			I_{GDsink} = 20mA			0.3	V
t_r	7	Output Voltage Rise Time	C_L = 1nF		40	100	ns
t_f	7	Output Voltage Fall Time	C_L = 1nF		40	100	ns
$I_{GD\ off}$	7	I_{GD} Sink Current	V_{CC} =3.5V V_{GD} = 1V	5	10	-	mA

OUTPUT OVERVOLTAGE SECTION

I_{OVP}	2	OVP Triggering Current		35	40	45	µA
		Static OVP Threshold		2.1	2.25	2.4	V

RESTART TIMER

t_{START}		Start Timer		70	150	400	µs

(1) Parameter guaranteed by design, not tested in production.

OVER VOLTAGE PROTECTION OVP

The output voltage is expected to be kept by the operation of the PFC circuit close to its nominal value. This is set by the ratio of the two external resistors R_1 and R_2 (see fig. 2), taking into consideration that the non inverting input of the error amplifier is biased inside the L6561 at 2.5V.

In steady state conditions, the current through R1 and R2 is:

$$I_{R1sc} = \frac{V_{out} - 2.5}{R1} = I_{R2} = \frac{2.5V}{R2}$$

and, if the external compensation network is made only with a capacitor C_{comp}, the current through C_{comp} equals zero.
When the output voltage increases abruptly the current through R1 becomes:

$$I_{R1} = \frac{V_{outsc} + \Delta V_{OUT} - 2.5}{R1} = I_{R1sc} + \Delta I_{R1}$$

Since the current through R2 does not change, ΔI_{R1} must flow through the capacitor C_{comp} and enter the error amplifier.

This current is monitored inside the L6561 and when reaches about 37µA the output voltage of the multiplier is forced to decrease, thus reducing the energy drawn from the mains. If the current exceeds 40µA, the OVP protection is triggered (Dynamic OVP), and the external power transistor is switched off until the current falls approximately below 10µA.

However, if the overvoltage persists, an internal comparator (Static OVP) confirms the OVP condition keeping the external power switch turned off (see fig. 1).
Finally, the overvoltage that triggers the OVP function is:

$$\Delta Vout = R_1 \cdot 40\mu A.$$

Typical values for R_1, R_2 and C are shown in the application circuits. The overvoltage can be set independently from the average output voltage. The precision in setting the overvoltage threshold is 7% of

the overvoltage value (for instance ΔV = 60V ± 4.2V).

Disable function

The zero current detector (ZCD) pin can be used for device disabling as well. By grounding the ZCD voltage the device is disabled reducing the supply current consumption at 1.4mA typical (@ 14.5V supply voltage).

Releasing the ZCD pin the internal start-up timer will restart the device.

Figure 1.

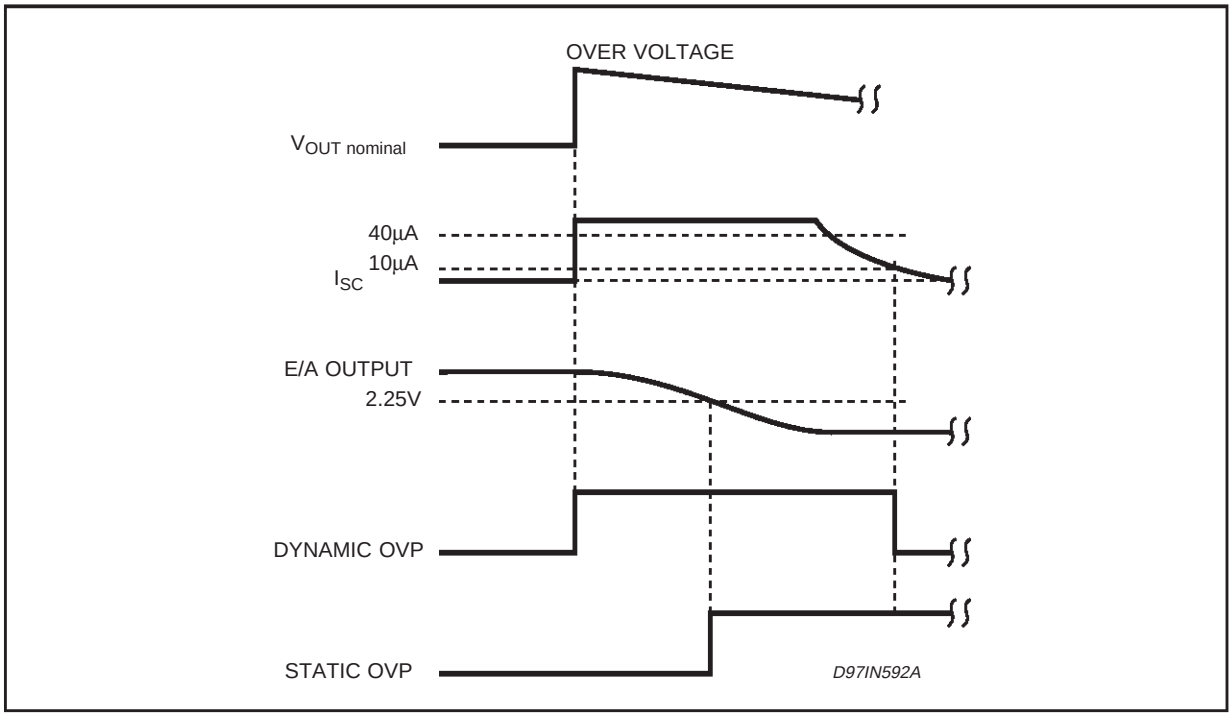


Figure 2. Overvoltage Protection Circuit

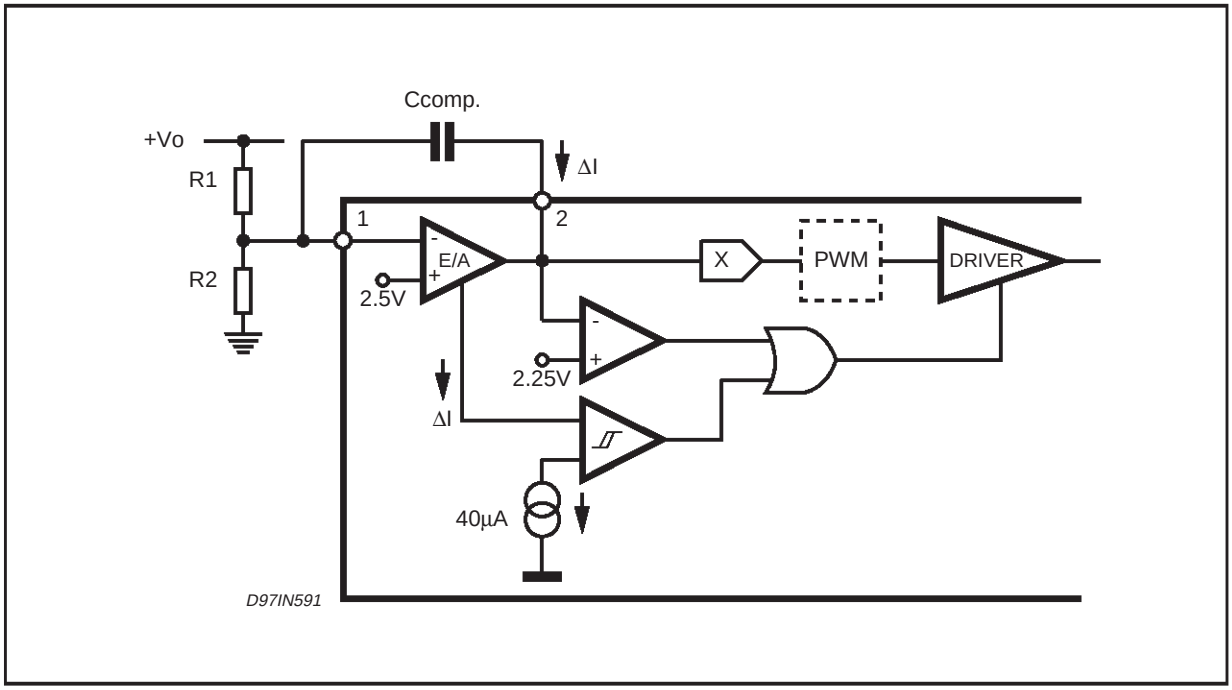


Figure 3. Typical Application Circuit (80W, 110VAC)

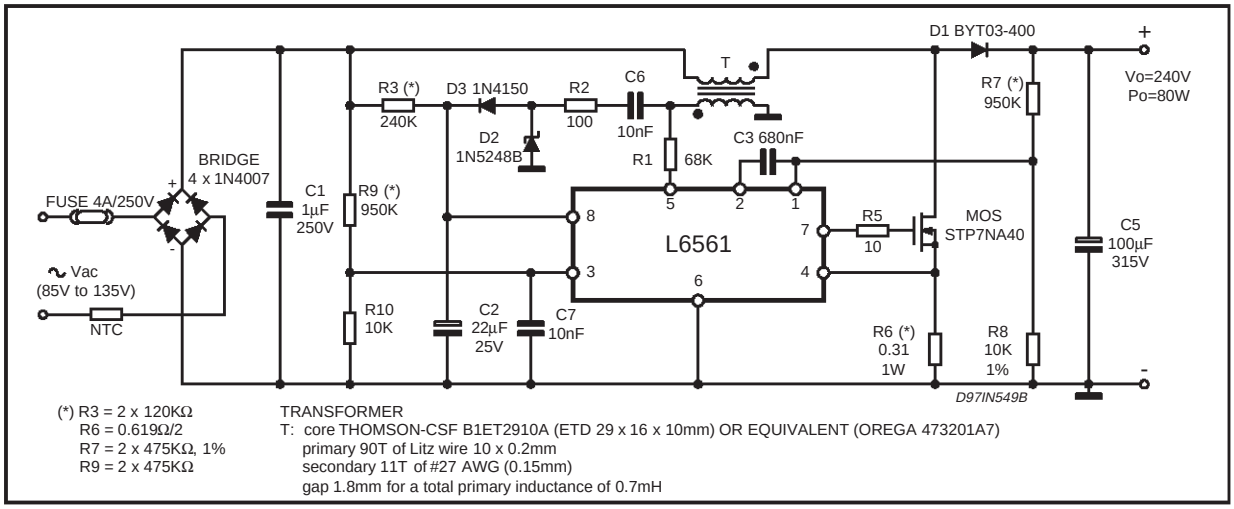


Figure 4. Typical Application Circuit (120W, 220VAC)

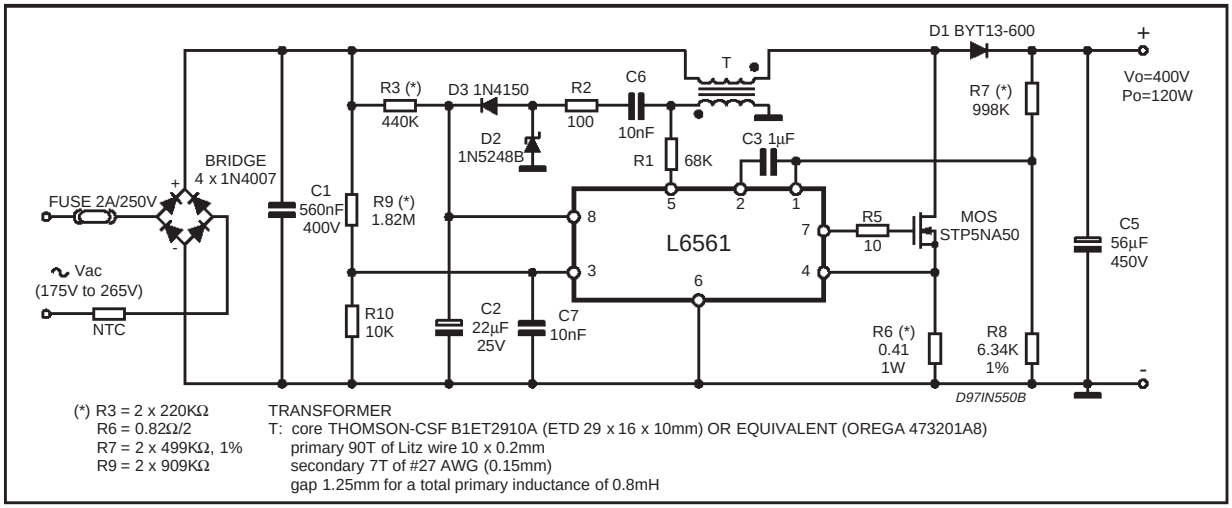


Figure 5. Wide-Range Application (80W)

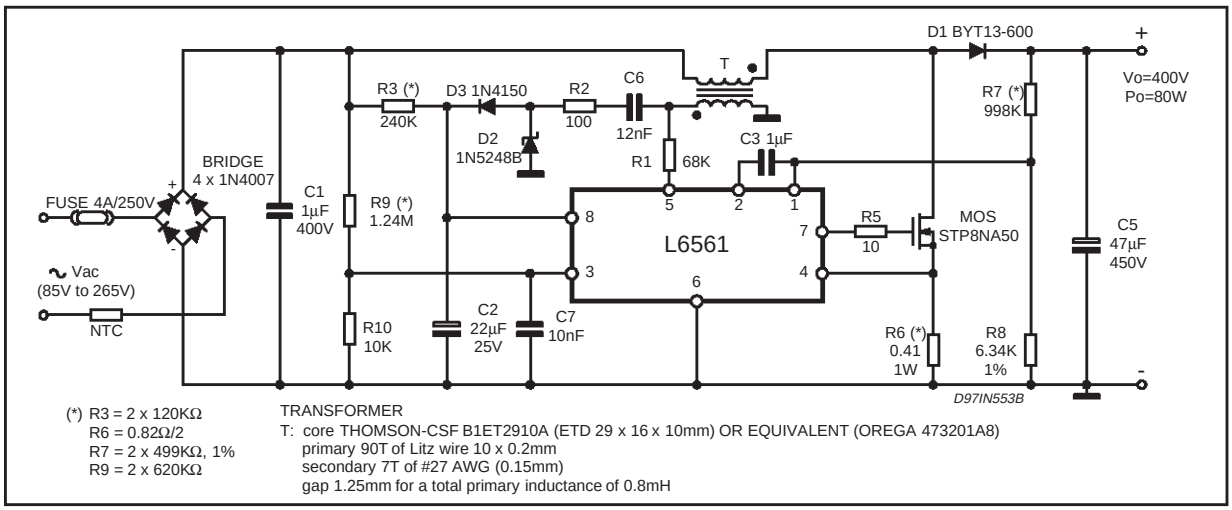


Figure 6. P.C. Board and Components Layout of the Figg. 3, 4 and 5 (1:1.25 scale)

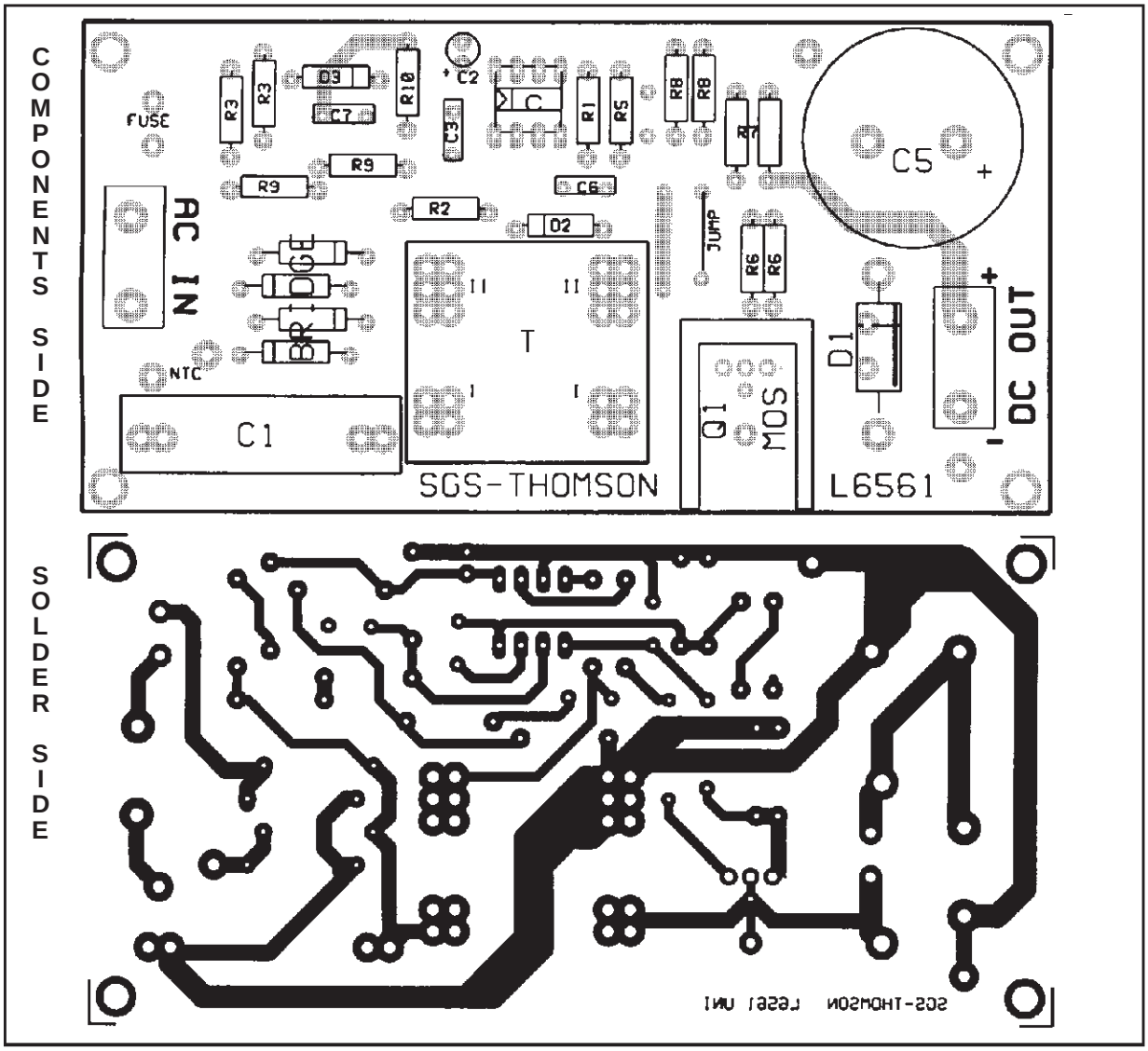


Figure 7. OVP Current Threshold vs. Temperature

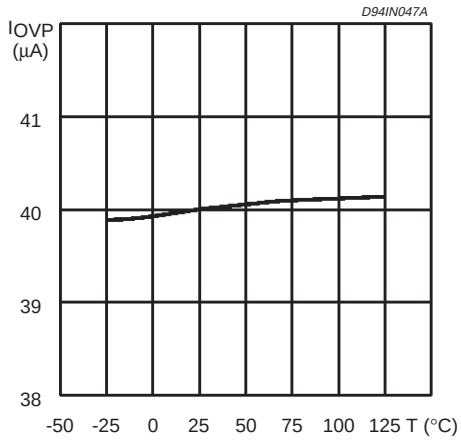


Figure 8. Undervoltage Lockout Threshold vs. Temperature

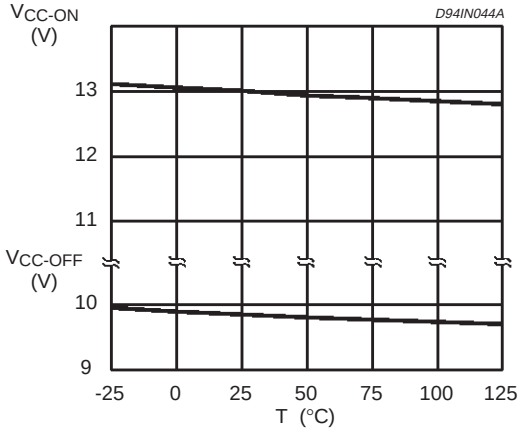


Figure 9. Supply Current vs. Supply Voltage

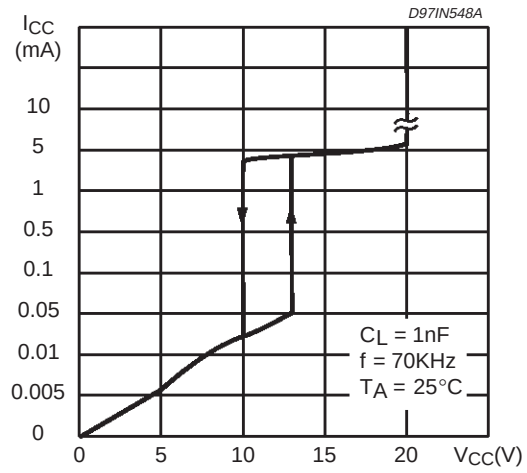


Figure 10. Voltage Feedback Input Threshold vs. Temperature

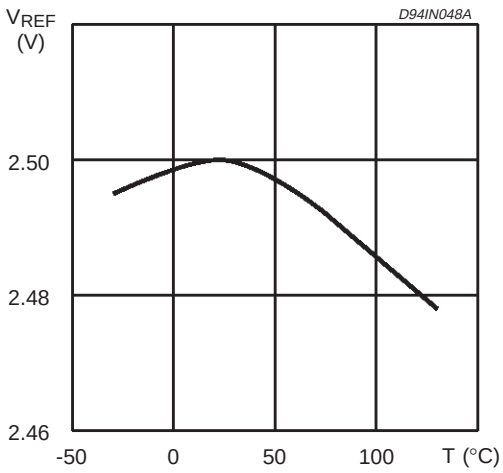


Figure 11. Output Saturation Voltage vs. Sink Current

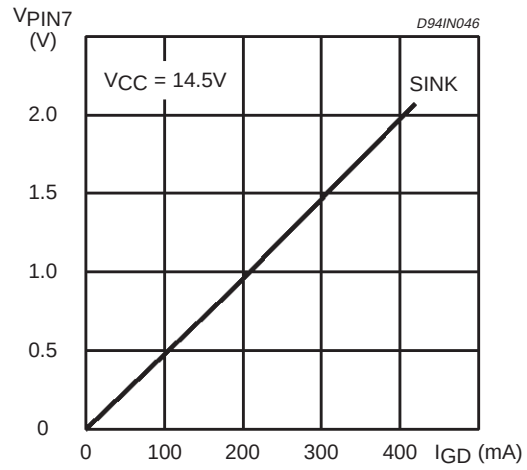


Figure 12. Output Saturation Voltage vs. Source Current

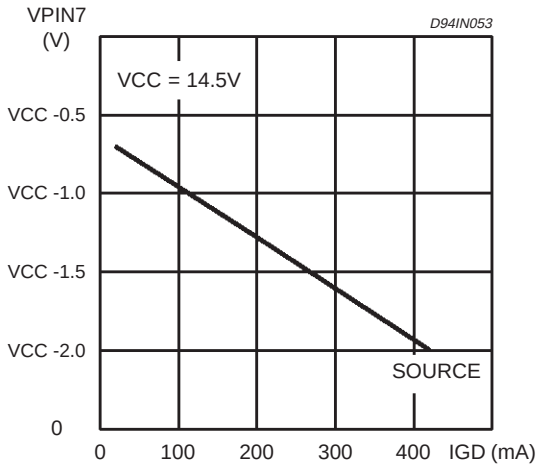
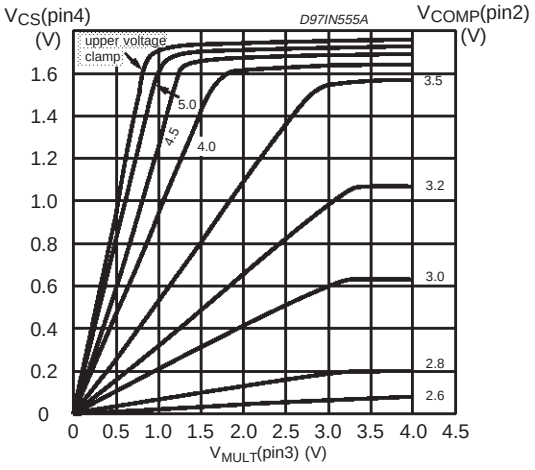
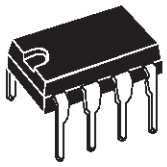


Figure 13. Multiplier Characteristics Family

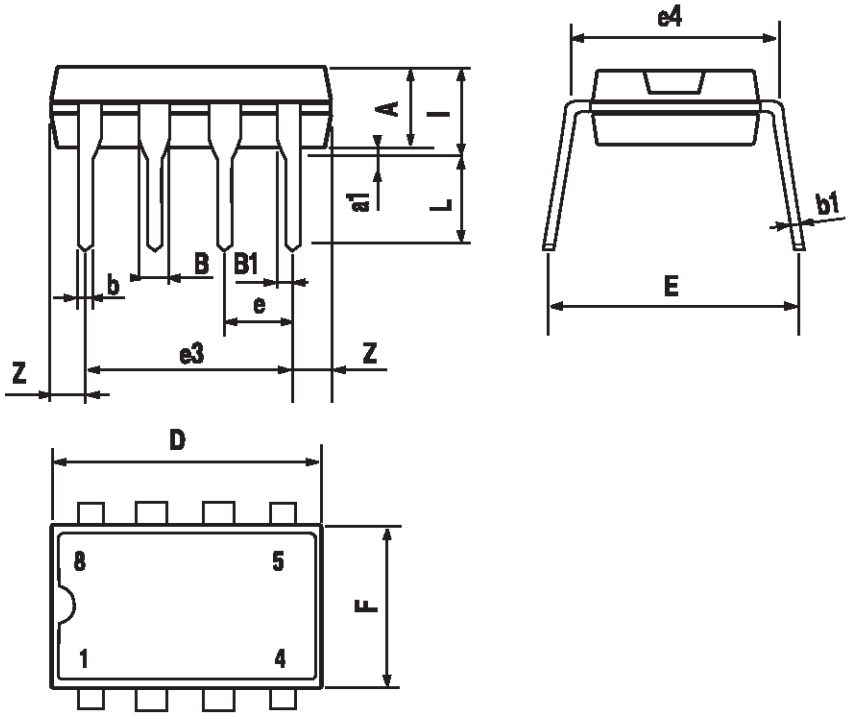


DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
I			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060

OUTLINE AND MECHANICAL DATA



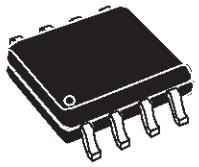
Minidip



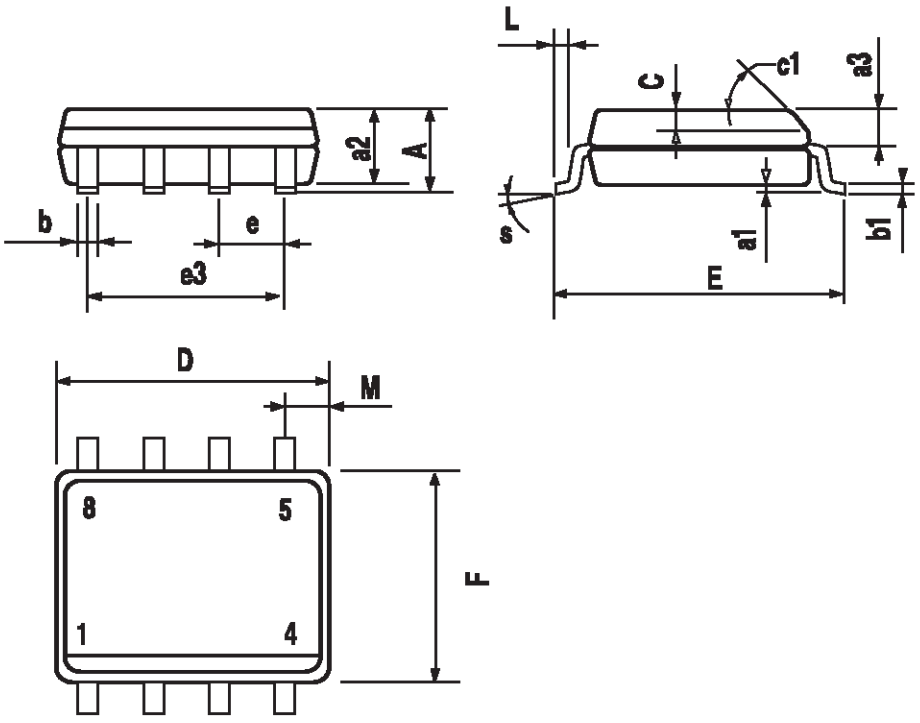
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.020
c1	45° (typ.)					
D (1)	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F (1)	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max.)					

(1) D and F do not include mold flash or protrusions. Mold flash or potrusions shall not exceed 0.15mm (.006inch).

OUTLINE AND MECHANICAL DATA



SO8



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